#### 1. General Description

The HAL206 is fabricated from mixed signal CMOS technology. It internally includes an on-chip Hall voltage generator, a voltage regulator for operation with supply voltages of 1.8 to 5.5V, a sleep/awake logic for low power consumption, temperature compensation circuitry, small-signal amplifier, Hall sensor with dynamic offset cancellation system, Schmitt trigger and an open-drain output. A south pole of sufficient strength will turn the sensor output on. The output will be turned off under no magnetic field. While the magnetic flux density (B) is larger than operating point (Bop), the output will be turned on (low), the output is held until B is lower than release point (Brp), and then turned off.

The total power consumption in normal operation is typically 15µW with a 3.3V power source. Operating temperature range of the HAL206 is from -40°C to 85°C.

#### 2. Features and Benefits

CMOS Hall IC Technology

Strong RF noise protection

1.8 to 5.5V for battery-powered applications

Micropower consumption

Multi Small Size option

Low sensitivity drift in crossing of Temp. range Ultra Low power consumption at 8uA (Avg)

High ESD Protection, HBM> +/- 4KV( min ) Totem-pole output

Package: TO-92S, SOT23-3, SOT553, DFN1216-4L

## 3.Applications

Solid state switch

Handheld Wireless Handset Awake Switch (Flip Cell/PHS Phone/Note Book/Flip Video Set)

Magnet proximity sensor for reed switch replacement in low duty cycle applications

Speed sensor

Rope Skipper

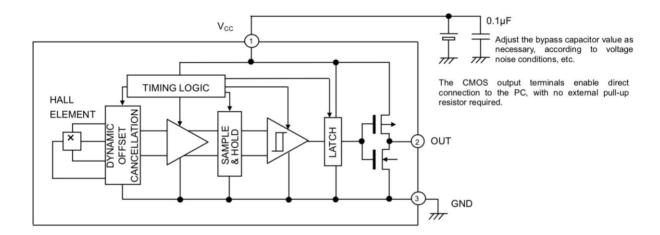
**BLDC Motor** 

## 4. Typical Application Circuit

Our pole-independent sensing technique allows for operation with either a north pole or south pole magnet orientation, enhancing the manufacturability of the device. The state-of-the-art technology provides the same output polarity for either pole face.

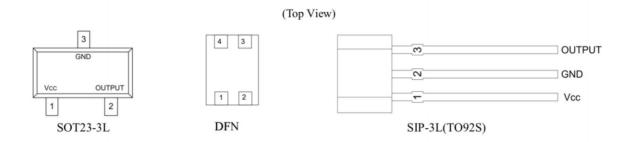
It is strongly recommended that an external bypass capacitor be connected (in close proximity to the Hall sensor) between the supply and ground of the device to reduce both external noise and noise generated by the chopper-stabilization technique. This is especially true due to the relatively high impedance of battery supplies.

## 5. Functional Block Diagram





# 6. Pinning



SOT Pin Number	SIP Pin Number	Pin Name	Function
1	1	VCC	Supply Voltage
2	3	OUT	CMOS Output
3	2	GND	Ground
4	NC		

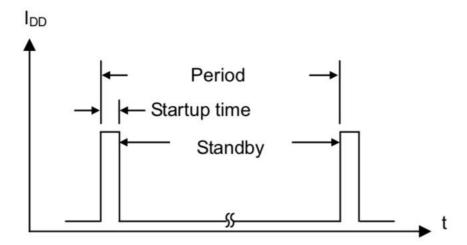
#### **SOT553**



SOT Pin Number	SIP Pin Number	Pin Name	Function
1	1	VCC	Supply Voltage
2	3	OUT	CMOS Output
3	3 2		Ground
4	NC		



#### 7. DESCRIPTION of OPERATIONS

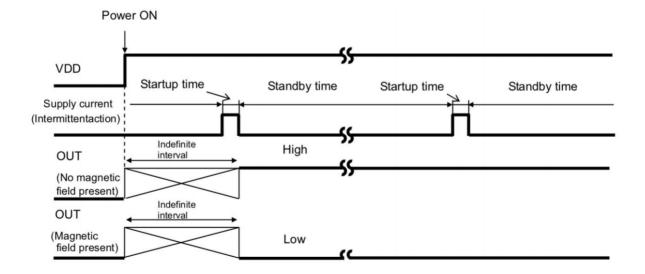


The unipolar detection Hall IC adopts an intermittent operation method to save energy. At startup, the Hall elements, amp, comparator and other detection circuit power ON and magnetic detection begins. During standby, the detection circuits power OFF, thereby reducing current consumption. The detection results are held while standby is active, and then output.

Reference period: 8ms (MAX10ms) Reference startup time: 50µs

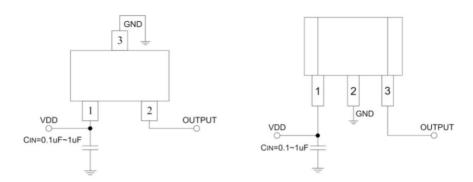
#### INTERMITTENT OPERATION at POWER ON

The unipolar detection Hall IC adopts an intermittent operation method in detecting the magnetic field during startup, as shown in Fig.5. It outputs to the appropriate terminal based on the detection result and maintains the output condition during the standby period. The time from power ON until the end of the initial startup period is an indefinite interval, but it cannot exceed the maximum period, 100ms. To accommodate the system design, the Hall IC output read should be programmed within 100ms of power ON, but after the time allowed for the period ambient temperature and supply voltage.





# 8. Typical Application Circuit



CMOS Bipolar High Sensitivity Micropower Hall Switch

Note: C<sub>IN</sub> is for power stabilization and to strengthen the noise immunity, the recommended capacitance is 0.1~1uF.

## 9. Absolute Maximum Ratings

Parameter	Symbol	Value	Units
Supply Voltage(operating)	$V_{DD}$	6	V
Supply Current	I <sub>DD</sub>	1	mA
Output Voltage	$V_{OUT}$	6	V
Output Curent	I <sub>OUT</sub>	1	mA
Operating Temperature Range	T <sub>A</sub>	-40 to 85	°C
Storage Temperature Rang	Ts	-50 to 150	°C
ESD Sensitivity	-	4000	V

Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute-maximum rated conditions for extended periods may affect device reliability.

## 10. Magnetic Characteristics

Operating Parameters: T<sub>A</sub> = 25 °C, V<sub>DD</sub>=2.75V<sub>DC</sub>.

PARAMETER	Symbol	Min	Туре	Max	Units
Operating Point	Вор	-	+25	50	Gs
Release Point	Brp	5	-25	-	Gs
Hysteresis	Bhys	-	50	-	Gs



# 10. DC Electrical Characteristics

DC Operating Parameters:  $T_A = 25^{\circ}C$ ,  $V_{DD}=2.75V$ .

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Operating voltage	$V_{DD}$	Operating	1.8	3.3	5.5	V
Output High Voltage	VOH	B <brps iout="-0.5mA&lt;/td"><td>VDD-0.2</td><td>-</td><td>-</td><td></td></brps>	VDD-0.2	-	-	
Output Low Voltage	VOL	BopS <b iout="+0.5mA&lt;/td"><td>-</td><td>-</td><td>0.2</td><td></td></b>	-	-	0.2	
Supply current1	I <sub>DD1 (AVG)</sub>	V <sub>DD</sub> =1.8V, Average	-	5	-	μΑ
Supply Current During Startup Time 1	I <sub>DD1 (EN)</sub>	V <sub>DD</sub> =1.8V, During Startup Time Value	-	1	-	mA
Supply Current During Standby Time 1	I <sub>DD1 (DIS)</sub>	V <sub>DD</sub> =1.8V, During Standby Time Value	-	3	-	μΑ
Supply current1	IDD1 (AVG)	V <sub>DD</sub> =3.0V, Average	-	8	-	μA
Supply Current During Startup Time 1	I <sub>DD1 (EN)</sub>	V <sub>DD</sub> =3.0V, During Startup Time Value	-	1.5	-	mA
Supply Current During Standby Time 1	I <sub>DD1 (DIS)</sub>	V <sub>DD</sub> =3.0V, During Standby Time Value	-	5	-	μΑ
Awake mode time	$T_AW$	Operating	-	25	-	μS
Sleep mode time	$T_SL$	Operating	-	8	10	mS

#### 12. Field Direction Definition

#### DFN1616 /SOT23-3 package

N pole near the marked side of the package, output low voltage. S pole near the marked side of the package, output high voltage.

### TO-92S /SOT553 package

S pole near the marked side of the package, output low voltage. N pole near the marked side of the package, output high voltage.

If the device is powered on with a magnetic field strength between  $B_{RP}$  and  $B_{OP}$ , then the device output is determinate High. For UA package, if the field strength is greater than  $B_{OP}$ , then the output is pulled low. If the field strength is less than  $B_{RP}$ , the output is released. For SO package, however, if the field strength is less than  $B_{OP}$ , then the output is pulled low. If the field strength is greater than  $B_{RP}$ , the output is released.

#### 13. ESD Protection

Human Body Model (HBM) tests according to: Mil. Std. 883F method 3015.7

Doromotor	Symbol	Limit Values		Unit	Notes
Parameter	Symbol	Min	Max	Onit	Notes
ESD Voltage	V <sub>ESD</sub>		4	kV	

## 14. Unique Features

## **CMOS Hall IC Technology**

The chopper stabilized amplifier uses switched capacitor techniques to eliminate the amplifier offset voltage, which, in bipolar devices, is a major source of temperature sensitive drift. CMOS makes this advanced technique possible. The CMOS chip is also much smaller than a bipolar chip, allowing very sophisticated circuitry to be placed in less space. The small chip size also contributes to lower physical stress and less power consumption.

#### **Installation Comments**

Consider temperature coefficients of Hall IC and magnetics, as well as air gap and life time variations.

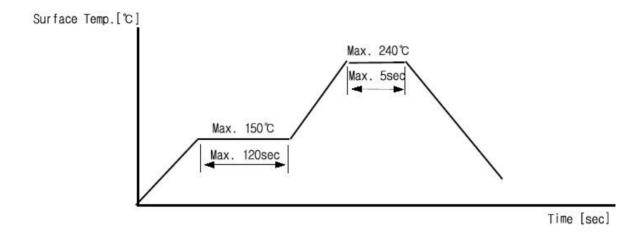


Observe temperature limits during wave soldering. Typical IR solder-reflow profile:

No Rapid Heating and Cooling.

Recommended Preheating for max. 2minutes at 150 C

Recommended Reflowing for max. 5seconds at 240 C

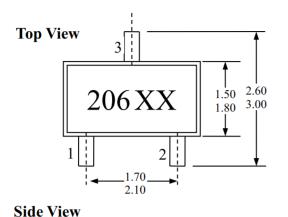


## 15. ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD). Always observe Electro Static Discharge control procedures whenever handling semiconductor products.

## 16. Package Information

## **SOT-23-3 Package Physical Characteristics**



**Notes:** 

1). PINOUT: Pin 1 VDD

Pin 2 Output

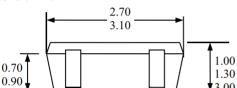
Pin 3 GND

2). All dimensions are in millimeters;

Marking:

206 -- Code of Device (HAL206);

XX: production code



0.35

0.50

3.00

3.0σ

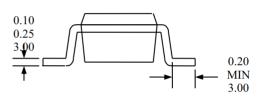
# **End View**

<u>13.0</u>0

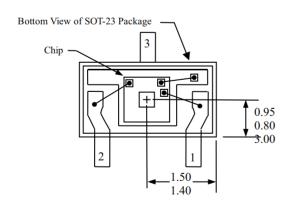
0.00

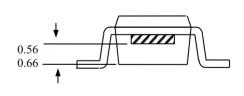
0.10

3.00



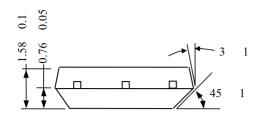
# **SOT-23-3 Package Hall Location**

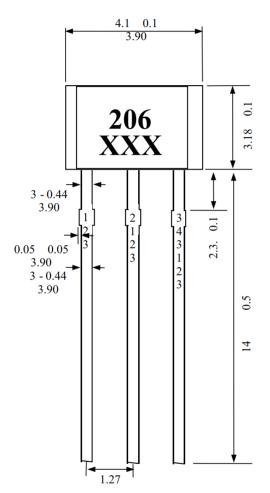


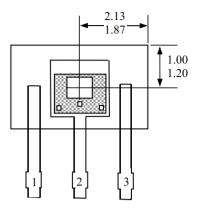




## 16.2 TO-92S Package Physical Characteristics







**Sensor Location** 

Active Area Depth: 0.84(Nom)

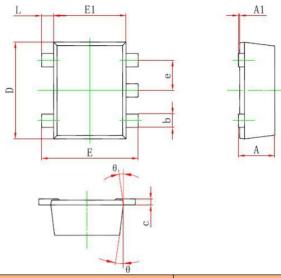
3 1 7 6 1

#### **Notes:**

- 1). Controlling dimension: mm;
- 2). Lesds must be free of flash and plating voids;
- 3). Do not bend leads within 1 mm of lead to package interface;
- 4). PINOUT: Pin 1 VDD
  - Pin 2 GND
  - Pin 3 Output



# 16.2 SOT553 Package Physical Characteristics



, mak al	Dimensions In Millimeters		Dimensions In Inches		
ymbol	Min.	Max.	Min.	Max.	
А	0.525	0.600	0.021	0.024	
A1	0.000	0.050	0.000	0.002	
е	0.450	0.550	0.018	0.022	
С	0.090	0.160	0.004	0.006	
D	1.500	1.700	0.059	0.067	
b	0.170	0.270	0.007	0.011	
E1	1.100	1.300	0.043	0.051	
E	1.500	1.700	0.059	0.067	
θ	7°REF		7°F	REF	
L	0.100	0.300	0.004	0.012	